



# DMMT5401

### MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

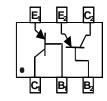
- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DMMT5551)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched PNP Pair (Note 1)

# 2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT) Lead Free/RoHS Compliant (Note 4) "Green" Device (Note 5 and 6)

#### **SOT-26** Dim Min Max Тур 0.50 Α 0.35 0.38 В 1.50 1.70 1.60 С 2.70 3.00 2.80 D 0.95 F 0.55 Н 3.00 2.90 3.10 J 0.10 0.05 0.013 1.30 1.10 K 1.00 L 0.55 0.40 0.35 М 0.10 0.20 0.15 0° 8° All Dimensions in mm

## **Mechanical Data**

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 6. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4S, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous (Note 2)	I <sub>C</sub>	-200	mA
Power Dissipation (Note 2, 3)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

#### Notes:

- Built with adjacent die from a single wafer. 1.
- Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

  Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

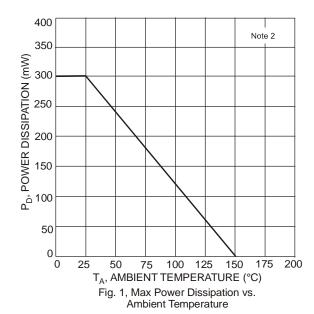


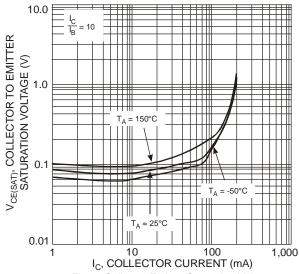
#### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-160	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-150	_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>		-50	nA μA	$V_{CB} = -120V, I_{E} = 0$ $V_{CB} = -120V, I_{E} = 0, T_{A} = 100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>	_	-50	nA	$V_{EB} = -3.0V, I_C = 0$
ON CHARACTERISTICS (Note 7)					
DC Current Gain (Note 8)	h <sub>FE</sub>	50 60 50	240 —	_	$I_C = -1.0$ mA, $V_{CE} = -5.0$ V $I_C = -10$ mA, $V_{CE} = -5.0$ V $I_C = -50$ mA, $V_{CE} = -5.0$ V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.2 -0.5	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$ $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	-1.0	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$ $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	6.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Small Signal Current Gain	h <sub>fe</sub>	40	200	_	$V_{CE} = -10V, I_{C} = -1.0mA,$ f = 1.0kHz
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE}$ = -5.0V, $I_{C}$ = -200 $\mu$ A, $R_{S}$ = 10 $\Omega$ , $f$ = 1.0kHz

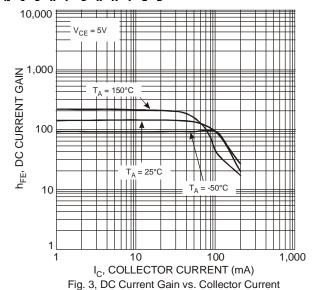
Notes:

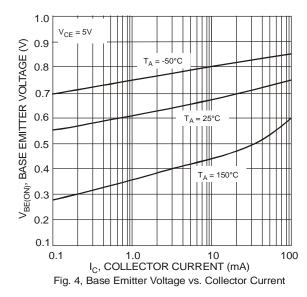
- Short duration pulse test used to minimize self-heating effect. The DC Current Gain,  $h_{FE}$ , (matched at  $I_C$  = -10mA and  $V_{CE}$  = -5V) Collector Emitter Saturation Voltage,  $V_{CE(SAT)}$ , and Base Emitter Saturation Voltage,  $V_{BE(SAT)}$  are matched with typical matched tolerances of 1% and maximum of 2%.











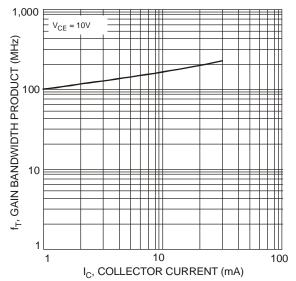


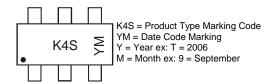
Fig. 5, Gain Bandwidth Product vs. Collector Current

# Ordering Information (Note 6 & 9)

Device	Packaging	Shipping
DMMT5401-7-F	SOT-26	3000/Tape & Reel

Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	J	٧	W	Χ	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

#### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.